

JHK100N120HA

Product Preview

**1200V/100A HIGH SPEED FIELD-STOP TRENCH IGBT
WITH DIODE**

Features

- Low $V_{CE(sat)}$
- Fast Switching
- High Ruggedness
- Short-Circuit Rated

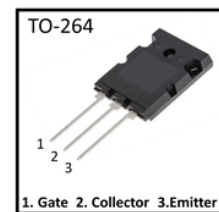
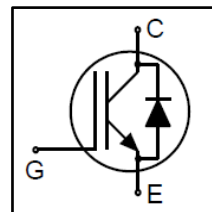


Product Summary

V_{CES}	1200V
I_C	100A ⁽¹⁾
$V_{CE(sat),typ}$	1.9V ($T_J = 25^\circ\text{C}$)
Package	TO-264

Applications

- Inverters
- Resonant Converters
- Induction Heating
- Power Supply



Ordering Information

Part Number	Marking	Package	Packing
JHK100N120HA	HK100N120HA	TO-264	Tube

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-to-Emitter Voltage	V_{CES}	1200	V
Gate-to-Emitter Voltage	V_{GES}	± 20	
DC Collector Current ($T_c = 25^\circ\text{C}$, $T_J = 175^\circ\text{C}$)	I_C	120 ⁽²⁾	A
DC Collector Current ($T_c = 95^\circ\text{C}$, $T_J = 175^\circ\text{C}$)		100	
Pulsed Collector Current (pulse width limited by maximum T_J)	I_{CM}	300	
Diode Forward Current ($T_c = 25^\circ\text{C}$, $T_J = 175^\circ\text{C}$)	I_F	120 ⁽²⁾	
Diode Forward Current ($T_c = 95^\circ\text{C}$, $T_J = 175^\circ\text{C}$)		100	
Diode Pulsed Current (pulse width limited by maximum T_J)	I_{FM}	300	
Short Circuit Withstand Time ($V_{GE} = 15\text{V}$, $V_{CC} \leq 600\text{V}$, $T_{J_start} \leq 175^\circ\text{C}$)	t_{SC}	10	μs
Turn-off Safe Operating Area ($V_{CE} \leq 1200\text{V}$, $T_J \leq 175^\circ\text{C}$)	-	300	A
Maximum Power Dissipation ($T_c = 25^\circ\text{C}$, $T_J = 175^\circ\text{C}$)	$P_{D(max)}$	625	W
Operating Junction Temperature	T_J	-40 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	
Maximum Lead Temperature for Soldering (1/8" from case for 5 seconds)	T_{slid}	260	

Static Electrical Characteristics ⁽³⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 250\mu A$	1200	-	-	V
Collector-to-Emitter Leakage Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0V$	-	-	10	μA
		$V_{CE} = 1200V, V_{GE} = 0V,$ $T_J = 175^\circ C$	-	-	10	mA
Gate-to-Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	100	nA
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 1.5mA$	5.5	6.5	7.5	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C = 100A$	-	1.9	2.3	
		$V_{GE} = 15V, I_C = 100A,$ $T_J = 175^\circ C$	-	2.7	-	
Diode Forward Voltage	V_F	$V_{GE} = 0V, I_F = 100A$	-	2.1	2.5	
		$V_{GE} = 0V, I_F = 100A$ $T_J = 175^\circ C$	-	1.9	-	

Thermal Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	-	-	25	$^\circ C/W$
Junction-to-Case Thermal Resistance, IGBT	$R_{\theta JC}$	-	-	0.24	
Junction-to-Case Thermal Resistance, Diode		-	-	0.31	

Dynamic Electrical Characteristics ⁽³⁾

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	$V_{CC} = 600V,$ $V_{GE} = 15V,$ $I_C = 100A$	-	319	-	nC
Input Capacitance	C_{iss}	$V_{CE} = 25V,$ $V_{GE} = 0V,$ $f = 1MHz$	-	7334	-	pF
Output Capacitance	C_{oss}		-	292	-	
Reverse Transfer Capacitance	C_{rss}		-	97	-	

Switching Characteristics, Inductive Load ^{(3), (4)}

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-on Delay time	$t_{d(ON)}$	$V_{CC} = 600V,$ $V_{GE} = 0/15V,$ $R_G = 1\Omega,$ $I_C = 100A,$ $L_{load} = 0.82mH,$ Energy losses include "tail" and diode reverse recovery.	-	57	-	ns
Rise Time	t_r		-	120	-	
Turn-off Delay time	$t_{d(OFF)}$		-	210	-	
Fall Time	t_f		-	105	-	
Turn-On Switching Loss	E_{on}		-	9.7	-	mJ
Turn-Off Switching Loss	E_{off}		-	4.1	-	
IGBT Total Switching Loss	E_{ts}		-	13.8	-	
Diode Reverse-Recovery Time	t_{rr}	$V_R = 600V,$ $I_F = 100A,$ $di_F/dt = -670A/\mu s$	-	344	-	ns
Diode Reverse-Recovery Charge	Q_{rr}		-	4730	-	nC
Diode Peak Reverse-Recovery Current	I_{rrm}		-	29	-	A
Short Circuit Collector Current	$I_{C(SC)}$	$V_{GE} = 15V,$ $V_{CC} \leq 600V,$ $t_{SC} \leq 10\mu s$	-	370	-	A

(1) DC collector current, $T_c = 95^\circ C$, $T_j = 175^\circ C$.

(2) Limited by bonding wire

(3) $T_j = 25^\circ C$ unless otherwise specified

(4) t_r : from 10% of I_C to 90% of I_C ; t_f : from 90% of I_C to 10% of I_C ;

E_{on} : from 10% of V_{GE} to 10% of V_{CE} ; E_{off} : from 90% of V_{GE} to 10% of I_C .

Typical Electrical Characteristics

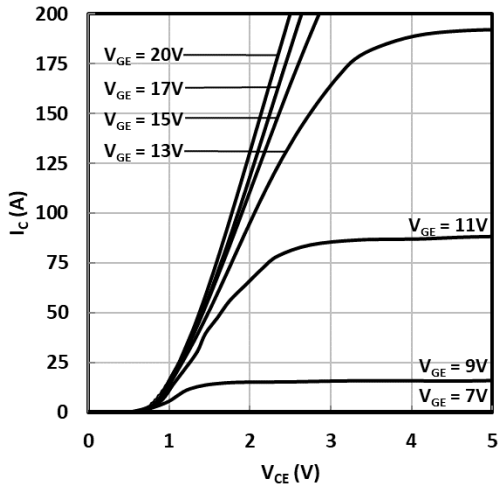


Fig. 1 Typical output characteristics
($T_j = 25\text{ }^\circ\text{C}$, $t_p = 250\text{ }\mu\text{s}$)

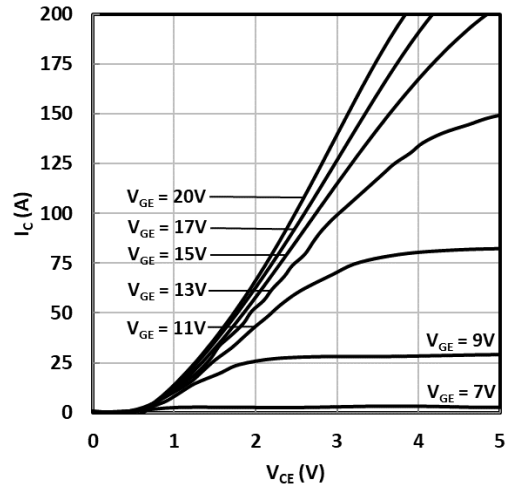


Fig. 2 Typical output characteristics
($T_j = 175\text{ }^\circ\text{C}$, $t_p = 250\text{ }\mu\text{s}$)

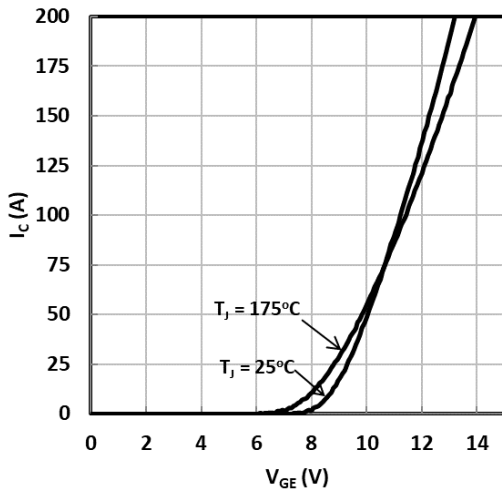


Fig. 3 Typical transfer characteristics
($V_{ce} = 20\text{ V}$, $t_p = 250\text{ }\mu\text{s}$)

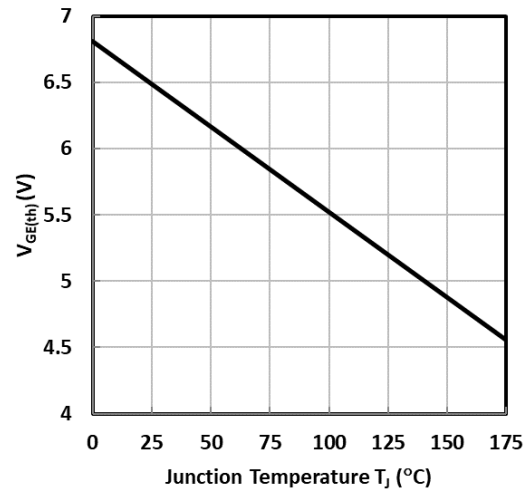


Fig. 4 Typical gate threshold voltage as a function of junction temperature
($V_{ce} = V_{ge}$, $I_c = 1.5\text{ mA}$)

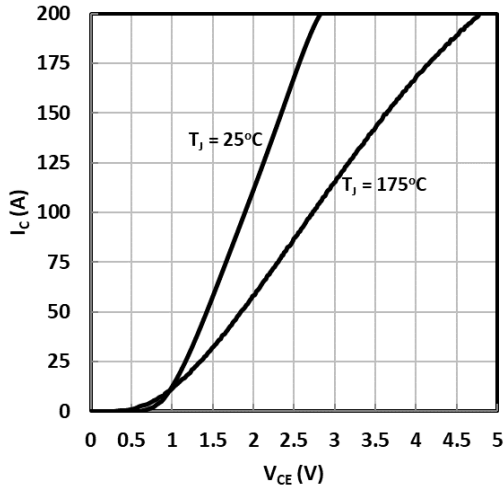


Fig. 5 Typical saturation voltage characteristics
($V_{GE} = 15\text{ V}$, $t_p = 250\ \mu\text{s}$)

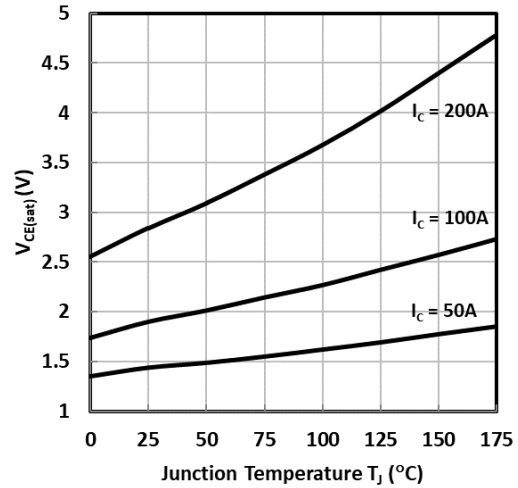


Fig. 6 Typical saturation voltage as a function of junction temperature
($V_{GE} = 15\text{ V}$, $t_p = 250\ \mu\text{s}$)

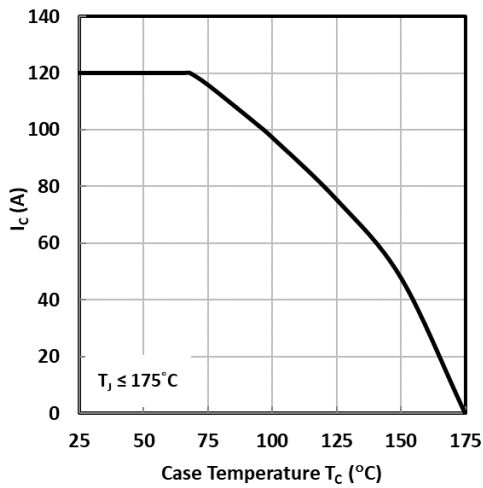


Fig. 7 Maximum DC collector current as a function of case temperature

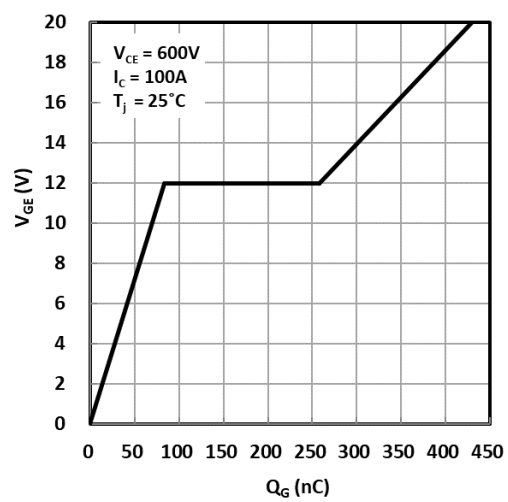


Fig. 8 Typical gate charge characteristics

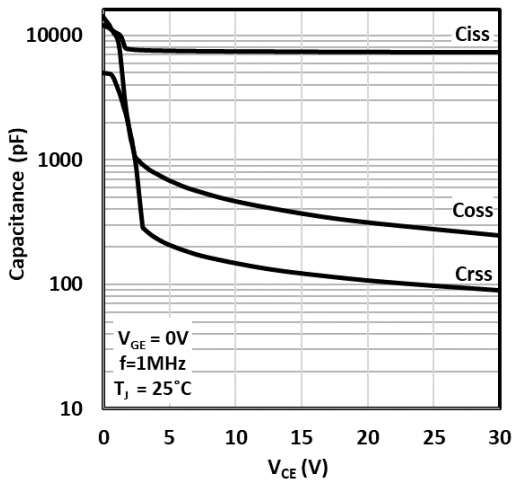


Fig. 9 Typical capacitance as a function of collector-to-emitter voltage

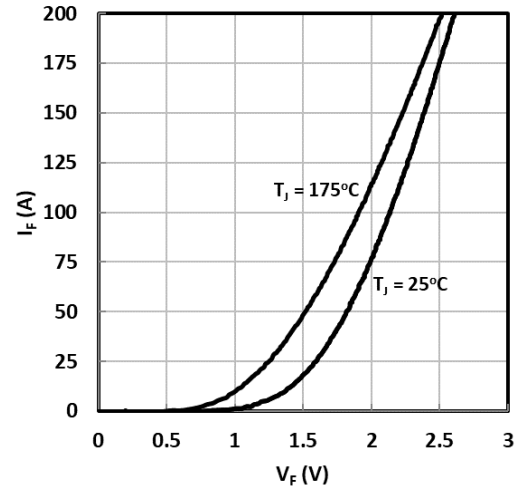


Fig. 10 Typical diode forward current as a function of forward voltage
($V_{GE} = 0\text{ V}$, $t_p = 250\ \mu\text{s}$)

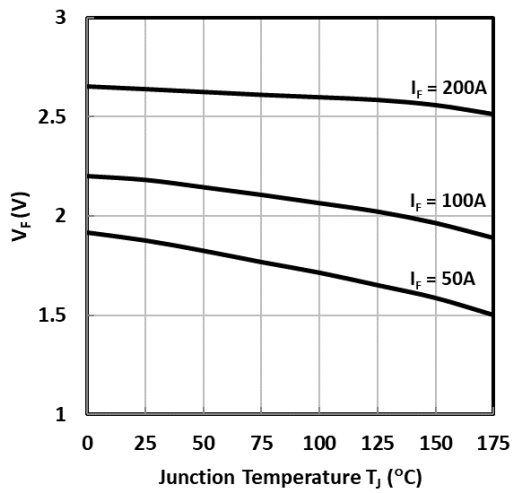
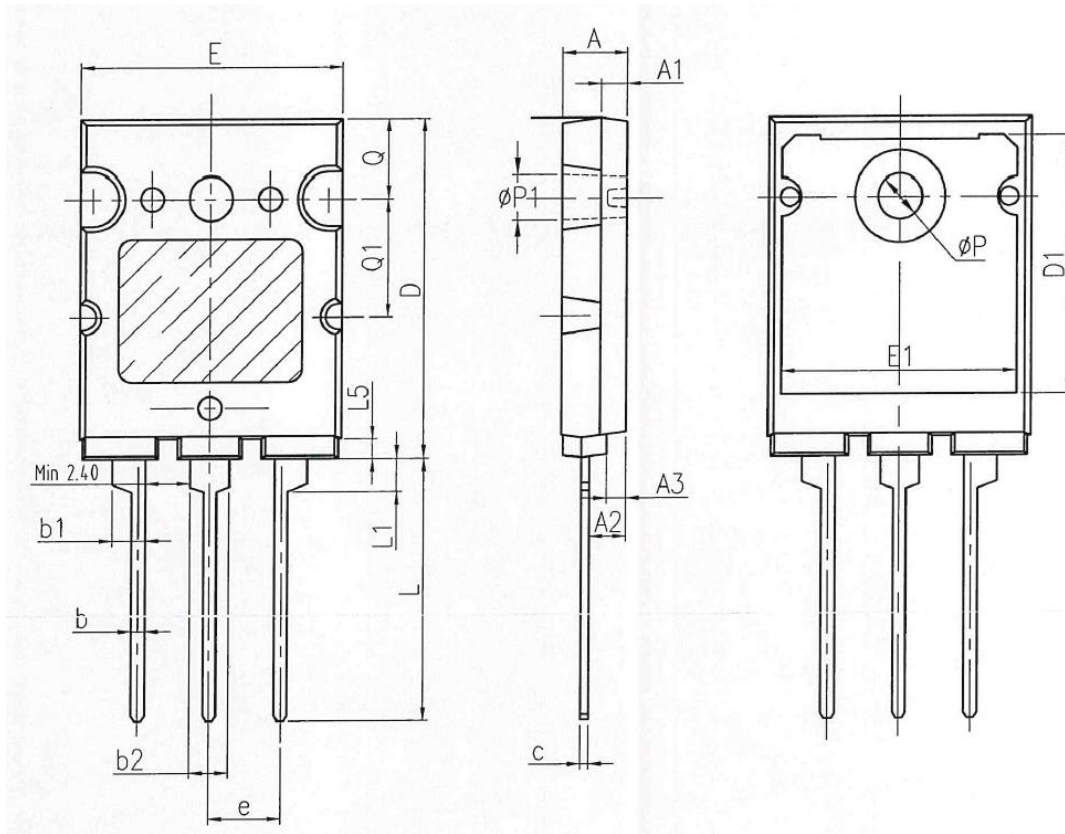


Fig. 11 Typical diode forward voltage as a function of junction temperature

Package Drawing



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.00		REF
A2	2.50	2.80	3.10
A3	1.50		REF
b	0.90	1.00	1.25
b1	2.30	2.50	2.75
b2	2.80	3.00	3.20
c	0.50	0.60	0.85
D	25.70	26.00	26.30
D1	19.00	-	-
E	19.50	20.00	20.50
E1	16.00	-	-
e	5.45 TYP		
L	19.50	20.00	20.50
L1	2.20	2.50	2.70
L5	1.35		REF
ΦP	3.00	3.20	3.40
ΦP1	3.20	3.40	3.60
Q	5.80	6.00	6.20
Q1	8.80	9.00	9.20

TO-264

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